

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of :
:
Kazuhiko YAMAMOTO :
:
Serial No.: Group Art Unit:
:
Filed: June 25, 2003 Examiner:
:
For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

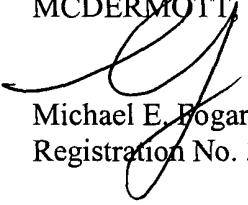
The relevance of two publications listed on attached Form 1449 is discussed in the present specification.

Serial No.:

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY


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INFORMATION DISCLOSURE CITATION IN AN APPLICATION			ATTY. DOCKET NO. 60188-606	SERIAL NO.			
			APPLICANT Kazuhiko YAMAMOTO				
(PTO-1449)			FILING DATE June 25, 2003	GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document			
		US					
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code ₃ -Number «-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		Shui-Hsiang Su et al. "A TWO-STEP DEPOSITION TECHNOLOGY FOR HIGH DIELECTRIC CONSTANT HfO ₂ THIN FILMS" Electrochemical and Solid-State Letters, 4(9), 2001, pp. F18-F19.					
		Yamamoto et al. "EFFECT OF HF METAL PREDEPOSITION ON THE PROPERTIES OF SPUTTERED HfO ₂ / HF STACKED GATE DIELECTRICS" Applied Physics Letters 81(11), 9 September 2002, pp. 2053-2055					
		Byoung Hun Lee et al. "ULTRATHIN HAFNIUM OXIDE WITH LOW LEAKAGE AND EXCELLENT RELIABILITY FOR ALTERNATIVE GATE DIELECTRIC APPLICATION" IEDM, 1999, pp. 133-136.					
EXAMINER				DATE CONSIDERED			

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.